

L Number	Hits	Search Text	DB	Time stamp
25	40	(high adj density adj plasma or HDP) near10 improv\$ same (deposit\$ and etch\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/17 09:35
-	23	US-4872947-\$.DID. OR US-4892753-\$.DID. OR US-4960488-\$.DID. OR US-5279865-\$.DID. OR US-5302233-\$.DID. OR US-5362526-\$.DID. OR US-0416048-\$.DID. OR US-5599740-\$.DID. OR US-0850105-\$.DID. OR US-0872052-\$.DID. OR US-6030881-\$.DID. OR US-6170428-\$.DID. OR US-6182602-\$.DID. OR US-6189483-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 10:58
-	22	dep\$1etch\$1dep	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:18
-	0	depost\$4 near3 etch\$4 near4 deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:18
-	0	depost\$1etch\$4deposition	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:18
-	9	deposition\$1etching\$1deposition	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:20
-	15100	plasma near10 deposit\$4 and plasma near10 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:20
-	53580	plasma near10 deposit\$4 sameplasma near10 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:20
-	9197	plasma near10 deposit\$4 same plasma near10 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:20
-	6037	plasma near5 deposit\$4 same plasma near5 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:21
-	115	plasma near5 deposit\$4 same plasma near5 etch\$4 same in\$1situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:21
-	26	(plasma near5 deposit\$4 same plasma near5 etch\$4 same in\$1situ) same (silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:21
-	16	continuous near10 in\$1situ same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:59

-	15	continuous near10 in\$1situ same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 15:52
-	15	overlap\$5 near5 flow\$4 same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:03
-	8604	deposit\$4 near10 etch\$4 near10 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:04
-	144	deposit\$4 near10 etch\$4 near10 plasma same in\$1situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:04
-	9	deposit\$4 near10 etch\$4 near10 plasma same in\$1situ same (overlap\$5 or continu\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:37
-	21	PECVD same (silicon adj dioxide or silicon adj nitride) same (fluoride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:40
-	670	PECVD same (silicon adj dioxide or silicon adj nitride) same silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:40
-	275	PECVD same (silicon adj dioxide or silicon adj nitride) near10 silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:40
-	0	PECVD same (silicon adj dioxide or silicon adj nitride) near10 silane near10 fluorine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:40
-	38	PECVD same (silicon adj dioxide or silicon adj nitride) near10 fluorine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 17:08
-	11	poloidal near4 ion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 17:11
-	8	"1158565"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 17:11
-	722	in\$1situ near3 etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:26
-	1	in\$1situ near3 etch\$ and toroidal near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:27

-	83	etch\$ and toroidal near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:27
-	9	etch\$ and toroidal near3 plasma same parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:35
-	8	toroidal near3 plasma and cox.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:33
-	68	toroidal near3 plasma same parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:36
-	49	toroidal near3 plasma same parallel and poloidal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:36
-	25	toroidal near3 plasma same parallel same poloidal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:42
-	85	parallel same poloidal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:42
-	6	(parallel same poloidal) and etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:49
-	7	poloidal near3 ion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 11:49
-	4169	continuous\$ near4 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 10:58
-	472	continuous\$ near4 plasma same etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 10:58
-	110	continuous\$ near4 plasma same etch\$ same (dep or deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:32
-	10	"dep/etch/dep"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:33
-	13013	deposit\$ near2 etch\$ near3 deposit\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:33

-	3219	deposit\$ near2 etch\$ near3 deposit\$ same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:33
-	679	deposit\$ near2 etch\$ near3 deposit\$ same plasma same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:33
-	170	deposit\$ near2 etch\$ near3 deposit\$ same plasma same silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:33
-	71	deposit\$ near2 etch\$ near3 deposit\$ near10 plasma same silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 11:48
-	32	deposit\$ near2 etch\$ near10 simultaneous\$ near10 plasma same silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 13:39
-	61	dep\$3etch\$3dep\$2 or deposit\$4etch\$4deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 13:17
-	21	(dep\$3etch\$3dep\$2 or deposit\$4etch\$4deposit\$4) same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 13:22
-	2	5270264.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 13:22
-	110	deposit\$ near2 etch\$ near10 simultaneous\$ near10 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 13:39
-	78	(deposit\$ near2 etch\$ near10 simultaneous\$ near10 plasma) not (deposit\$ near2 etch\$ near10 simultaneous\$ near10 plasma same silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:11
-	13	poloidal near5 ion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:13
-	411	poloidal same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:14
-	0	poloidal same plasma and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:14
-	20	poloidal near10 parallel same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:19

-	6	poloidal same plasma and applied.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 14:19
-	9	poloidal same plasma and etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 15:03
-	2	5252178.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 15:10
-	2	6167834.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 15:15
-	2	electrical near3 bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 15:15
-	5680	electrical near3 bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 15:15
-	85	electrical near3 bias same plasma same RF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:03
-	5553918	high enar2 density near3 plasma or HCP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:03
-	5553853	high enar2 density near3 plasma or HDP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:03
-	12061	high near2 density near3 plasma or HDP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:05
-	702	(high near2 density near3 plasma or HDP) same (deposit\$ or etch\$) same advantag\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:04
-	489	(high near2 density near3 plasma or HDP) same (deposit\$) same advantag\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:04
-	3	((high near2 density near3 plasma or HDP) same (deposit\$) same advantag\$) and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:04
-	9406	high adj density adj plasma or HDP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/14 16:05

-	162	(high adj density adj plasma or HDP) near10 advantag\$ same (deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 16:07
-	73	(high adj density adj plasma or HDP) near10 advantag\$ same (deposit\$ and etch\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 09:35